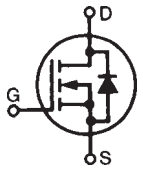
IXYS

Polar™ HiPerFET™ Power MOSFET

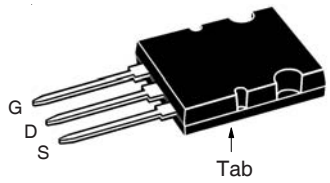
IXFB170N30P

V_{DSS} = 300V
I_{D25} = 170A
$R_{DS(on)}$ ≤ 18mΩ
t_{rr} ≤ 200ns

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode



PLUS264™



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	300	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	300	V
V_{GSS}	Continuous	±20	V
V_{GSM}	Transient	±30	V
I_{D25}	T_C = 25°C	170	A
I_{LRMS}	Leads Current Limit, RMS	160	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	500	A
I_A	T_C = 25°C	85	A
E_{AS}	T_C = 25°C	5	J
dv/dt	$I_S \le I_{DM}$, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$	20	V/ns
P_D	T_C = 25°C	1250	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	Plastic Body for 10s	260	°C
F_C	Mounting Force	30..120 / 6.7..27	N/lb
Weight		10	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 3mA	300			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 8mA	2.5		4.5	V
I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±200	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0V			25	μA
	T_J = 125°C			1.5	mA
$R_{DS(on)}$	V_{GS} = 10V, $I_D = 0.5 \bullet I_{D25}$, Note 1			18	mΩ

Features

- Fast Intrinsic Diode
- Avalanche Rated
- Very Low R_{th} Results High Power Dissipation
- Low $R_{DS(ON)}$
- Low Package Inductance

Advantages

- Low Gate Charge Results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dv/dt Ruggedness
- High Power Density

Applications

- DC-DC Coverters
- Battery Chargers
- Switched-Mode and Resonant-Mode Power Supplies
- DC Choppers
- AC and DC Motor Control
- Uninterrupted Power Supplies
- High Speed Power Switching Applications

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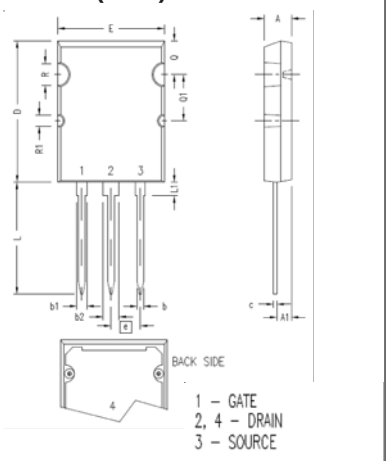
Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = 10V, I_D = 60A, Note 1	57	95		S
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		20		nF
C_{oss}			2450		pF
C_{rss}			27		pF
$t_{d(on)}$	**Resistive Switching Times**		41		ns
t_r	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D =0.5 • I_{D25}		29		ns
$t_{d(off)}$	R_G = 1Ω (External)		79		ns
t_f			16		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		258		nC
Q_{gs}			82		nC
Q_{gd}			78		nC
R_{thJC}				0.10	°C/W
R_{thCS}			0.13		°C/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0V			170	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			500	A
V_{SD}	I_F = 85A, V_{GS} = 0V, Note 1			1.3	V
t_{rr}	I_F = 85A, -di/dt = 150A/μs			200	ns
Q_{RM}	V_R = 100V		1.85		μC
I_{RM}			21		A

Note 1: Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

PLUS264™ (IXFB) Outline



SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,860,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ T_J = 25ºC

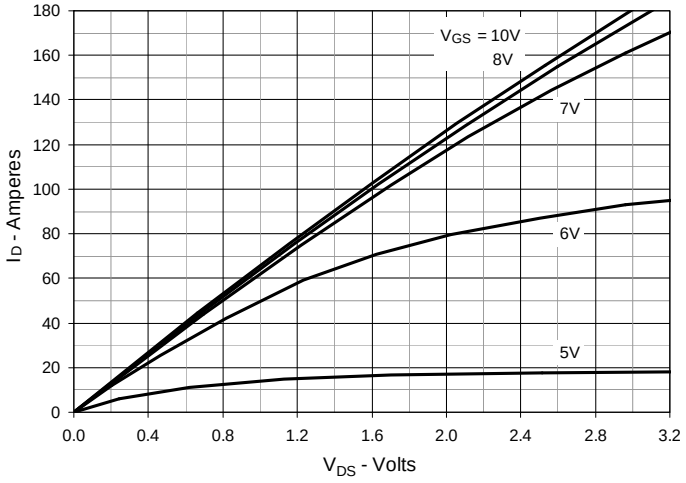


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

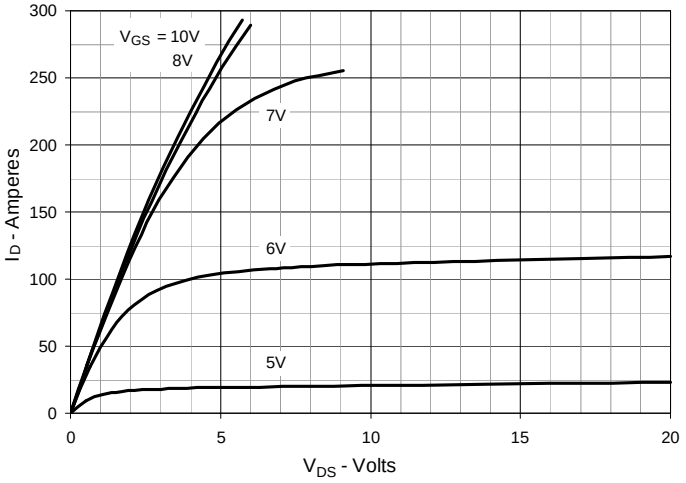


Fig. 3. Output Characteristics @ T_J = 125ºC

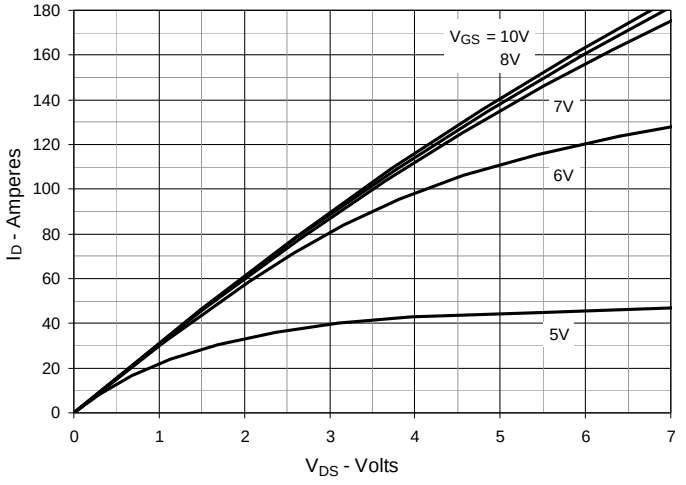


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 85A Value vs. Junction Temperature

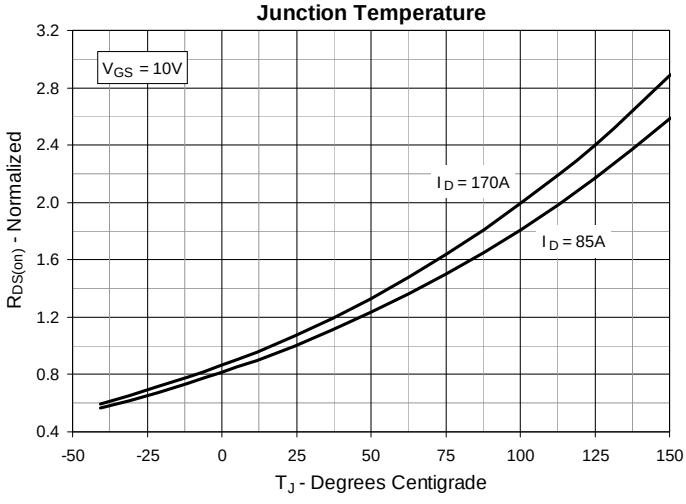


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 85A Value vs. Drain Current

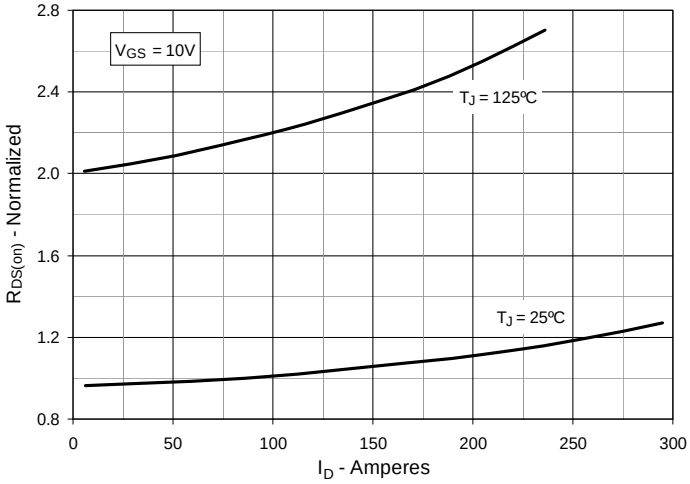
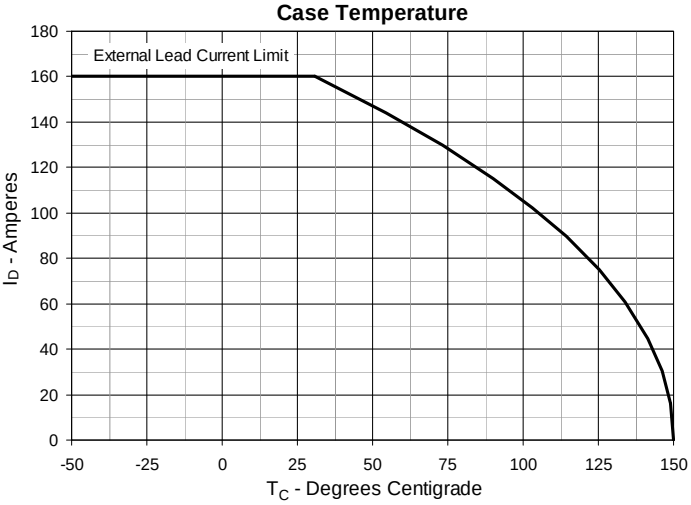


Fig. 6. Maximum Drain Current vs. Case Temperature



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Fig. 7. Input Admittance

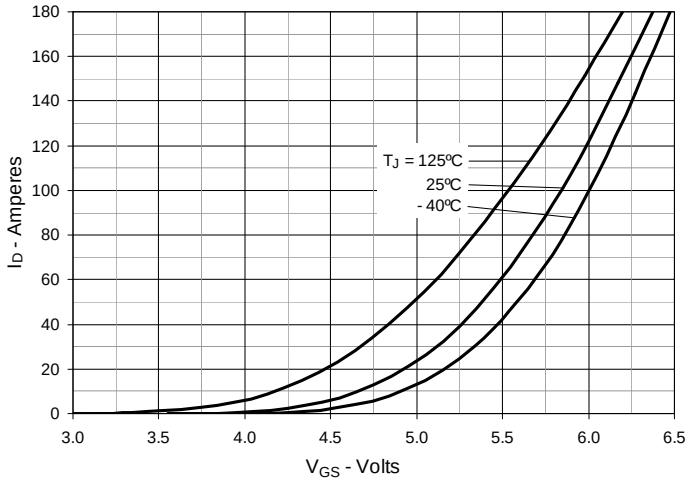


Fig. 8. Transconductance

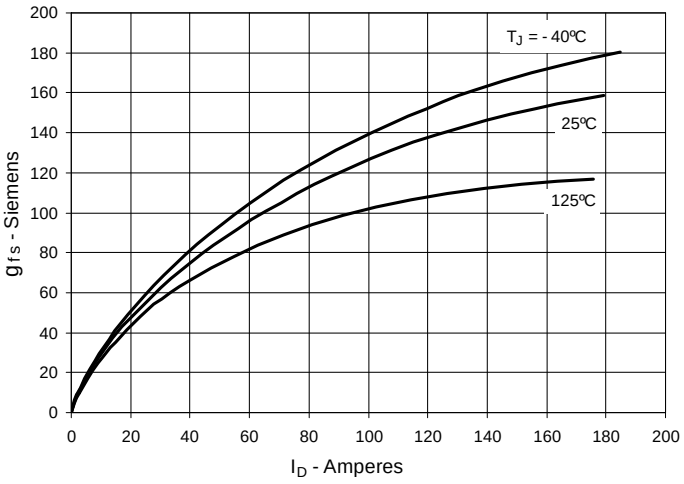


Fig. 9. Forward Voltage Drop of Intrinsic Diode

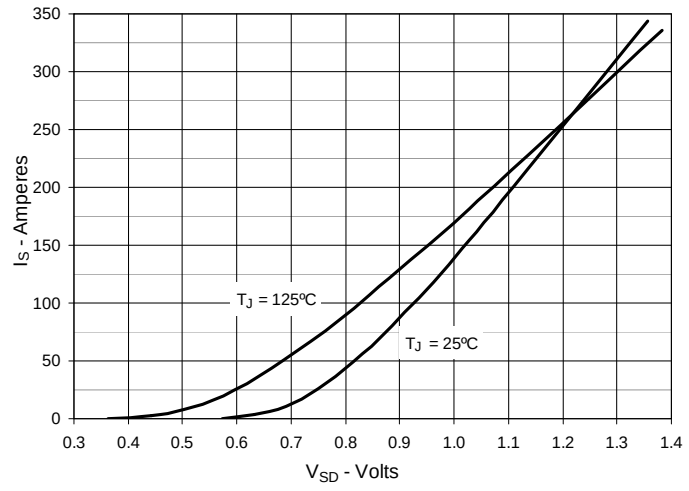


Fig. 10. Gate Charge

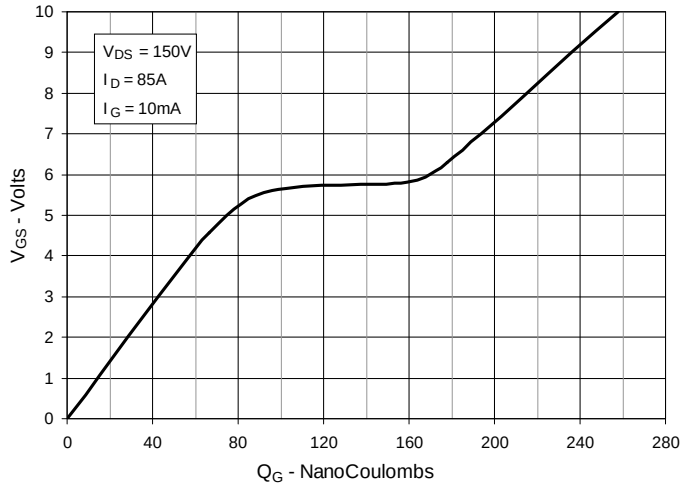


Fig. 11. Capacitance

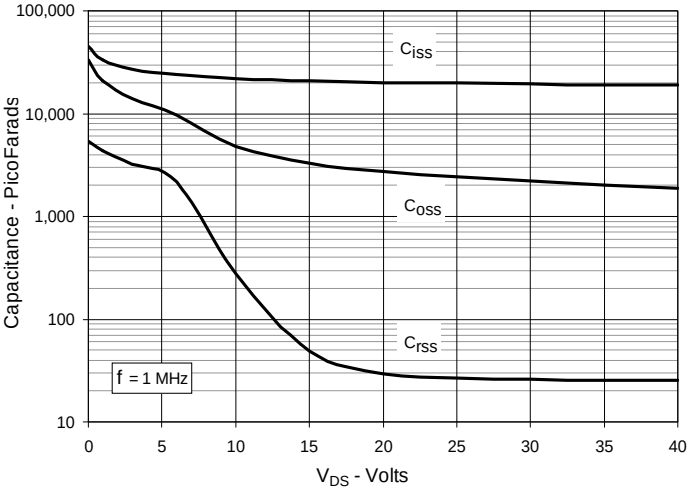
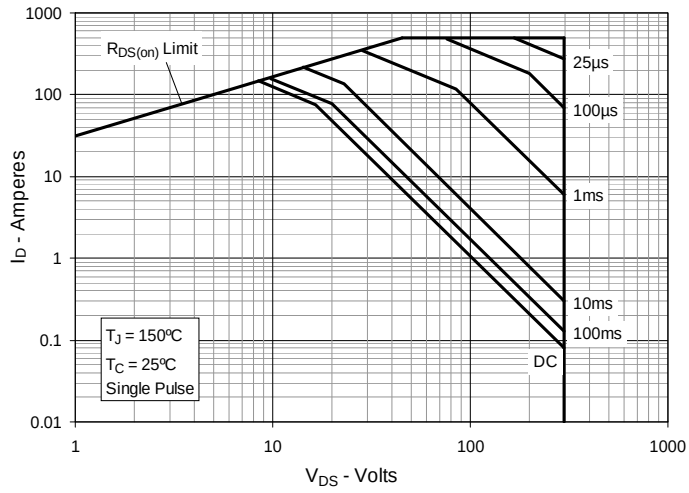
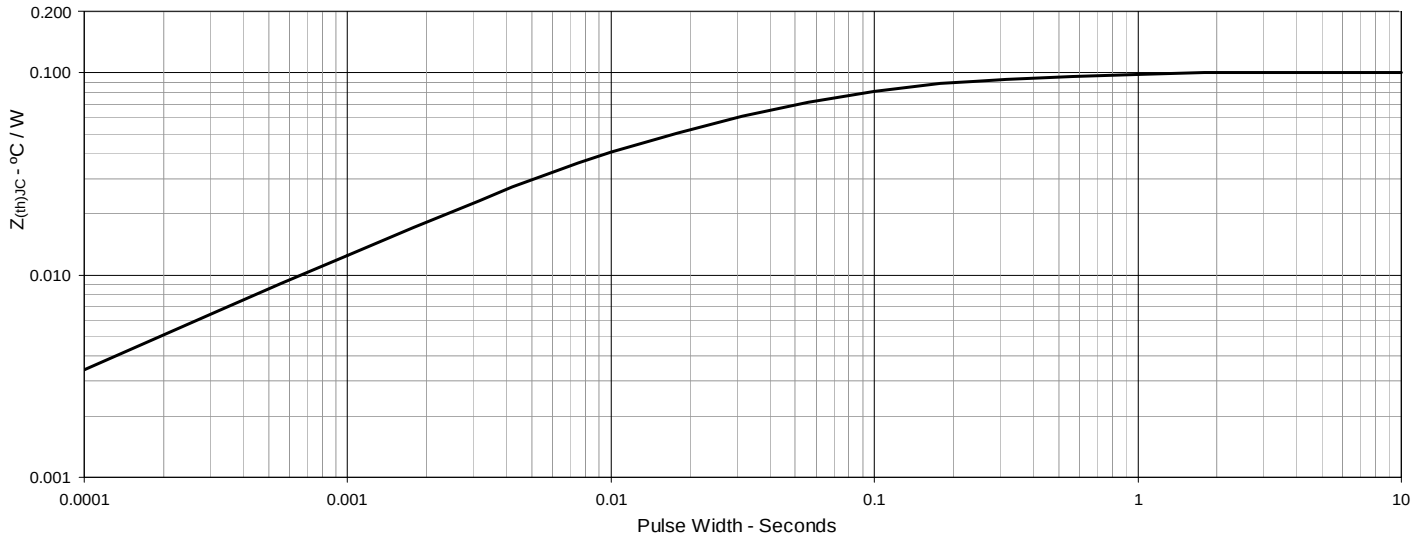


Fig. 12. Forward-Bias Safe Operating Area



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Fig.13. Maximium Transient Thermal Impedance



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